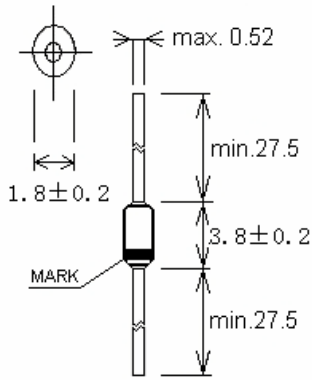




DO-35 Glass



Unit: mm

**DO-35 玻封稳压二极管**  
**DO-35 Glass Zener Diode**

**特征 Features**

- 反向漏电小; Low Reverse Leakage
- 齐纳击穿阻抗低; Low Zener Impedance
- 最大功率耗散 500mW; Power Dissipation of 500mW
- 高稳定性和可靠性。High Stability and High Reliability

**机械数据 Mechanical Data**

- 封装: DO-35 玻璃封装 Case: DO-35 Glass Case
- 极性: 色环端为负极 Polarity: Color band denotes cathode end
- 安装位置: 任意 Mounting Position: Any

**极限值和温度特性**( $T_A = 25^\circ\text{C}$  除非另有规定)

**Maximum Ratings & Thermal Characteristics** (Ratings at  $25^\circ\text{C}$  ambient temperature unless otherwise specified.)

参数 Parameters	符号 Symbol	数值 Value	单位 Unit
功率消耗 Power Dissipation	$P_d$	500 <sup>1)</sup>	mW
工作结温 Operating junction temperature	$T_j$	175	$^\circ\text{C}$
存储温度 Storage temperature range	$T_s$	-55-+175	$^\circ\text{C}$

1) Valid provided that leads are kept at ambient temperature at a distance of 8mm from case

**电特性** ( $T_A = 25^\circ\text{C}$  除非另有规定)

**Electrical Characteristics** (Ratings at  $25^\circ\text{C}$  ambient temperature unless otherwise specified).

型号 TYPE	稳压范围 Zener Voltage		反向电流 Reverse Current		动态电阻 Dynamic Resistance		
	$V_z(\text{V})$		$I_r(\mu\text{A})$	测试条件 Test Condition	$r_d(\Omega)$	测试条件 Test Condition	
	Min.	Max.	Max.	$V_r(\text{V})$	Max.	$I_z(\text{mA})$	
BZX55C 2V0	1.80	2.15	5.0	100	1.0	85	5.0
BZX55C 2V2	2.08	2.33	5.0	75	1.0	85	5.0
BZX55C 2V4	2.28	2.56	5.0	50	1.0	85	5.0
BZX55C 2V7	2.50	2.90	5.0	10	1.0	85	5.0
BZX55C 3V0	2.80	3.20	5.0	4	1.0	85	5.0
BZX55C 3V3	3.10	3.50	5.0	2	1.0	85	5.0
BZX55C 3V6	3.40	3.80	5.0	2	1.0	85	5.0
BZX55C 3V9	3.70	4.10	5.0	2	1.0	85	5.0
BZX55C 4V3	4.00	4.60	5.0	1	1.0	75	5.0
BZX55C 4V7	4.40	5.00	5.0	0.5	1.0	60	5.0
BZX55C 5V1	4.80	5.40	5.0	0.1	1.0	35	5.0
BZX55C 5V6	5.20	6.00	5.0	0.1	1.0	25	5.0
BZX55C 6V2	5.80	6.60	5.0	0.1	2.0	10	5.0
BZX55C 6V8	6.40	7.20	5.0	0.1	3.0	8	5.0
BZX55C 7V5	7.00	7.90	5.0	0.1	5.0	7	5.0
BZX55C 8V2	7.70	8.70	5.0	0.1	6.2	7	5.0



型号 TYPE	稳压范围 Zener Voltage		反向电流 Reverse Current		动态电阻 Dynamic Resistance		
	Vz(V)		测试条件 Test Condition	Ir(uA)	测试条件 Test Condition	rd(Ω)	测试条件 Test Condition
	Min.	Max.	Iz(mA)	Max.	Vr(V)	Max.	Iz(mA)
BZX55C 9V1	8.50	9.60	5.0	0.1	6.8	10	5.0
BZX55C 10	9.40	10.60	5.0	0.1	7.5	15	5.0
BZX55C 11	10.40	11.60	5.0	0.1	8.2	20	5.0
BZX55C 12	11.40	12.70	5.0	0.1	9.1	20	5.0
BZX55C 13	12.40	14.10	5.0	0.1	10.0	26	5.0
BZX55C 14	13.30	14.70	5.0	0.1	10.0	26	5.0
BZX55C 15	13.80	15.60	5.0	0.1	11.0	30	5.0
BZX55C 16	15.30	17.10	5.0	0.1	12.0	40	5.0
BZX55C 18	16.80	19.10	5.0	0.1	13.0	50	5.0
BZX55C 20	18.80	21.20	5.0	0.1	15.0	55	5.0
BZX55C 22	20.80	23.30	5.0	0.1	16.0	55	5.0
BZX55C 24	22.80	25.60	5.0	0.1	18.0	80	5.0
BZX55C 27	25.10	28.90	5.0	0.1	20.0	80	5.0
BZX55C 30	28.00	32.00	5.0	0.1	22.0	80	5.0
BZX55C 33	31.00	35.00	5.0	0.1	24.0	80	5.0
BZX55C 36	34.00	38.00	5.0	0.1	27.0	80	5.0
BZX55C 39	37.00	41.00	2.5	0.1	30.0	90	2.5

**Notes:**

- 1) Tested with pulses  $t_p = 20$  ms.
- 2) Valid provided that leads are kept at ambient temperature at a distance of 8 mm from case
- 3) The BZX55-C0V8 is a silicon diode with operation in forward direction. Hence, the index of all parameters should be "F" instead of "Z". Connect the cathode lead to the negative pole.
- 4)  $V_F(\text{Max})=1.20\text{V}@ I_F=100\text{mA}$

**Breakdown characteristics  $T_j = \text{constant}$  (pulsed)**

